



# ACE4494M

## N-Channel 100-V MOSFET

### Description

The ACE4494M uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch or in PWM applications. The source leads are separated to allow a Kelvin connection to the source, which may be used to bypass the source inductance.

### Features

- Low  $r_{DS(on)}$  trench technology
- Low thermal impedance
- Fast switching speed

### Applications

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

### Absolute Maximum Ratings

Parameter		Symbol	Limit	Units
Drain-Source Voltage		$V_{DS}$	100	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>a</sup>	$T_A=25^\circ\text{C}$	$I_D$	11	A
	$T_A=70^\circ\text{C}$		9	
Pulsed Drain Current <sup>b</sup>		$I_{DM}$	80	A
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	5	A
Power Dissipation <sup>a</sup>	$T_A=25^\circ\text{C}$	$P_D$	3.1	W
	$T_A=70^\circ\text{C}$		2.2	
Operating temperature / storage temperature		$T_J/T_{STG}$	-55~150	$^\circ\text{C}$

### THERMAL RESISTANCE RATINGS

Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10 \text{ sec}$	$R_{\theta JA}$	40	$^\circ\text{C/W}$
	Steady State		80	

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.  
 b. Pulse width limited by maximum junction temperature

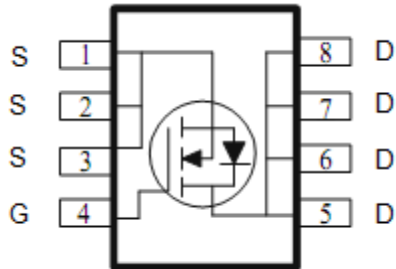


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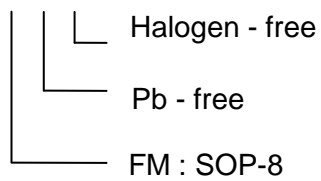
### Packaging Type

SOP-8



### Ordering information

ACE4494M FM + H





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### Electrical Characteristics

$T_A=25^{\circ}\text{C}$ , unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	1			V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			25	
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	16			A
Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 8.5 \text{ A}$			18	m $\Omega$
		$V_{GS} = 5.5 \text{ V}, I_D = 6.8 \text{ A}$			23	
Forward Transconductance	$g_{FS}$	$V_{DS} = 15 \text{ V}, I_D = 8.5 \text{ A}$		22		S
Diode Forward Voltage	$V_{SD}$	$I_S = 2.5 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 50 \text{ V}, V_{GS} = 5.5 \text{ V}, I_D = 8.5 \text{ A}$		60		nC
Gate-Source Charge	$Q_{gs}$			16		
Gate-Drain Charge	$Q_{gd}$			37		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 50 \text{ V}, R_L = 5.8 \Omega, I_D = 8.5 \text{ A},$ $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		26		ns
Rise Time	$t_r$			62		
Turn-Off Delay Time	$t_{d(off)}$			124		
Fall Time	$t_f$			60		
Input Capacitance	$C_{iss}$	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		4927		pF
Output Capacitance	$C_{oss}$			404		
Reverse Transfer Capacitance	$C_{rss}$			373		

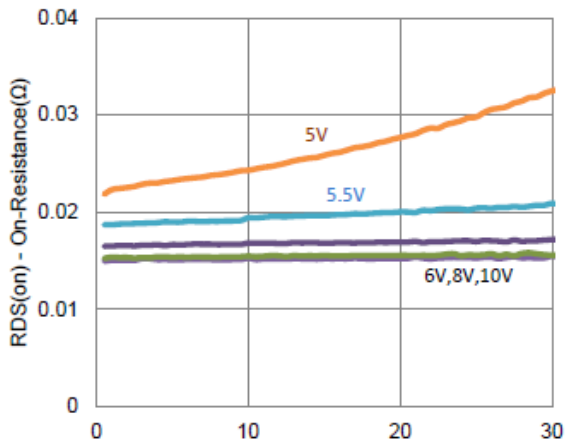
Note :

- Pulse test:  $PW \leq 300\mu\text{s}$  duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing

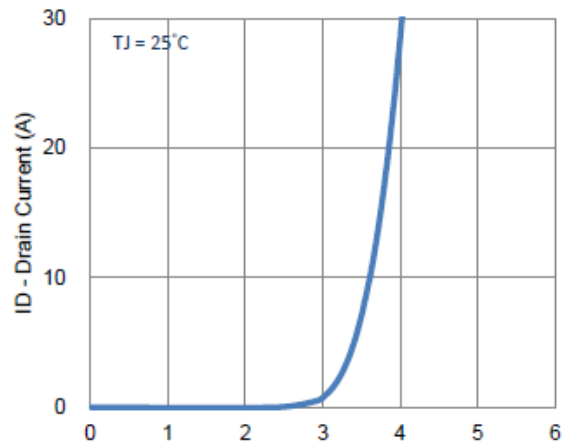


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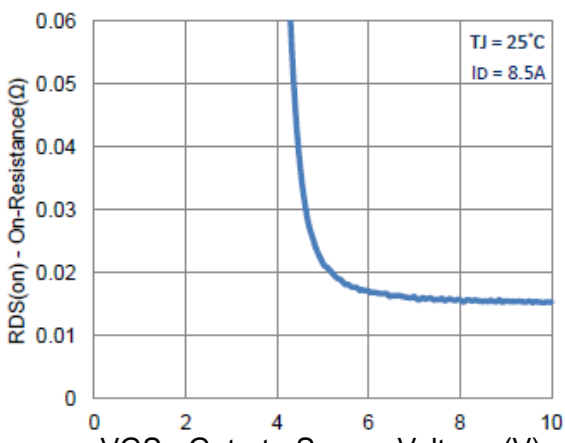
## Typical Performance Characteristics



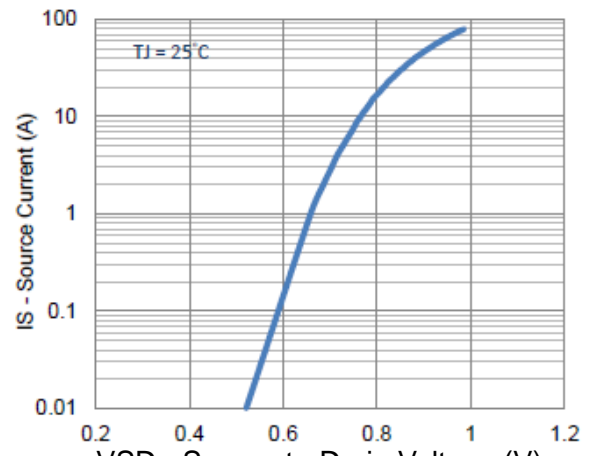
1. On-Resistance vs. Drain Current



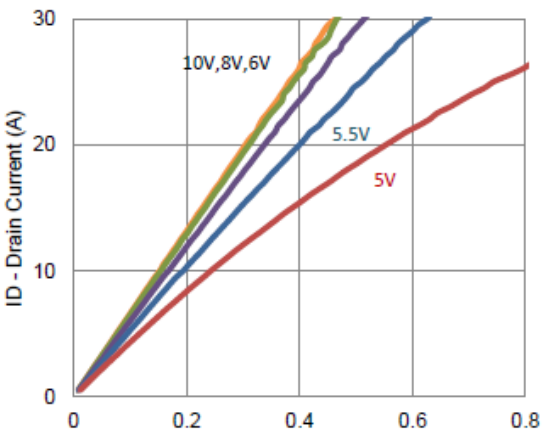
2. Transfer Characteristics



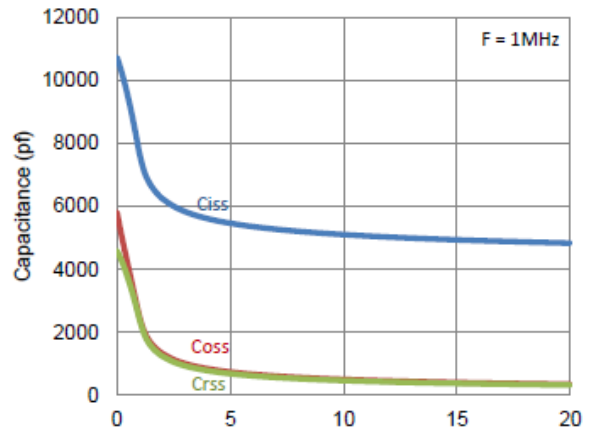
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage



5. Output Characteristics

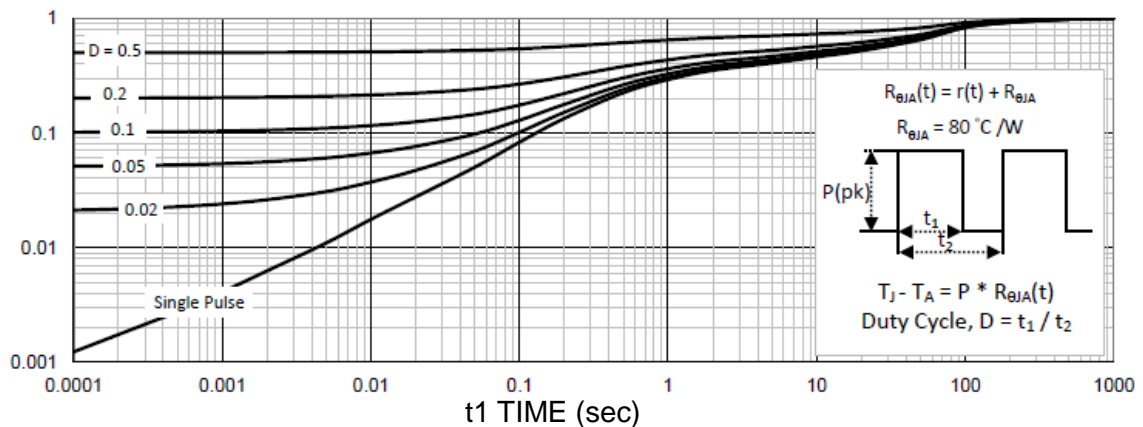
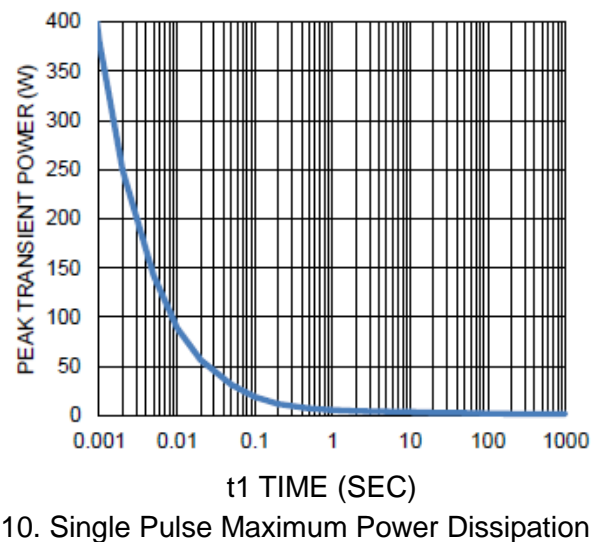
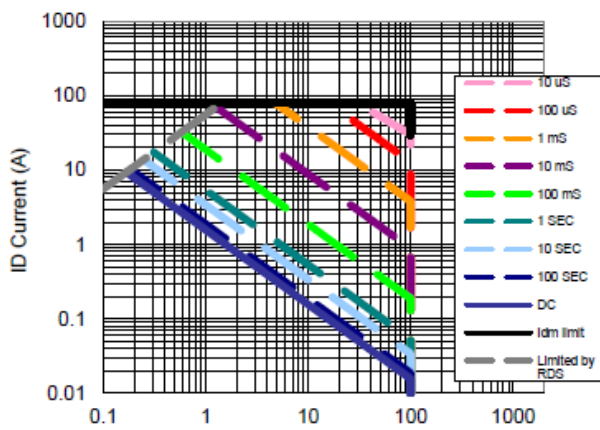
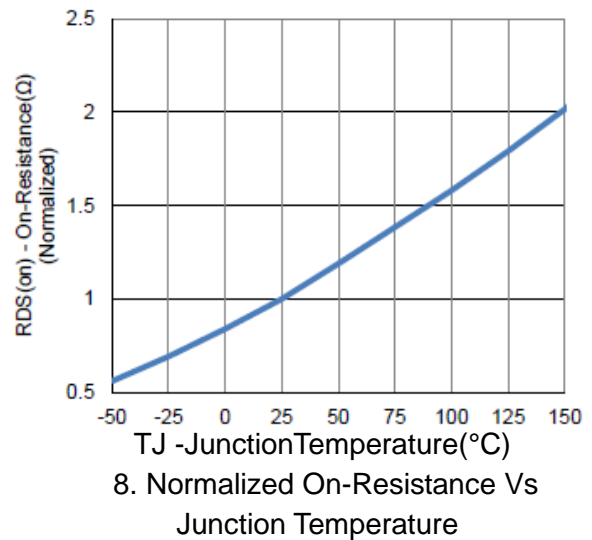
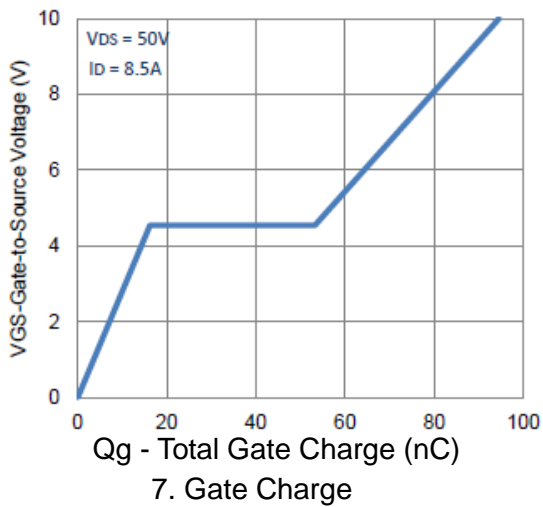


6. Capacitance



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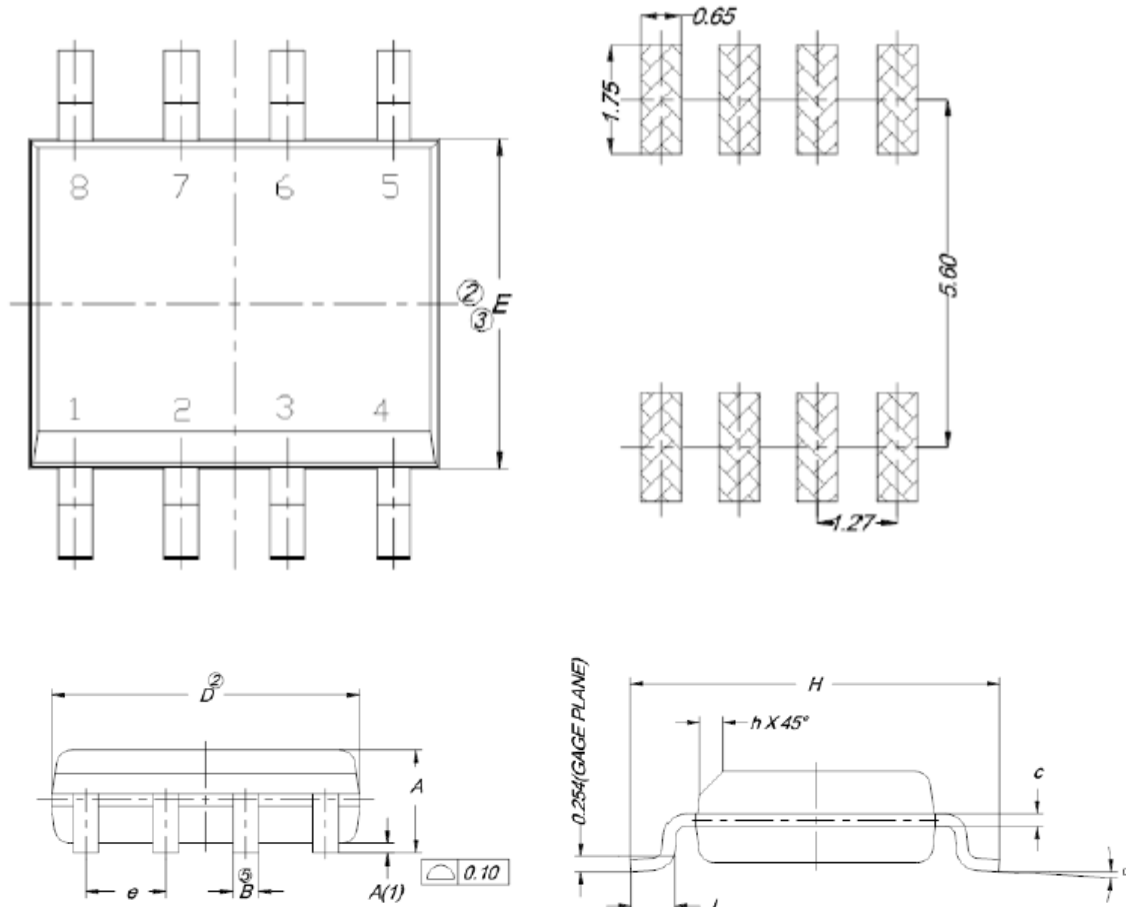


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### Packing Information

#### SOP-8



DIM	MILLMETERS		
	MIN	NOM	MAX
A	1.35	1.55	1.75
A(1)	0.10	0.18	0.25
B	0.38	0.45	0.51
C	0.19	0.22	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
e	1.27 BSC		
H	5.8	6.00	6.20
L	0.50	0.72	0.93
a	0°	4	8
h	0.25	0.38	0.50

Unit: mm



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### Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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